

PATENT**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

IN RE APPLICATION OF: ERIC J. BERGMAN
APPLICATION NO.: NOT YET ASSIGNED
FILED: OCTOBER 7, 2003
FOR: **METHODS FOR CLEANING SEMICONDUCTOR
SURFACES**

EXAMINER:
ART UNIT:
CONF. NO:

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

1. Timing of Submission

This information disclosure statement is being filed concurrently with the filing of the application. The references listed on the enclosed Form PTO-1449 (modified) may be material to the examination of this application; the Examiner is requested to make them of record in the application.

2. Cited Information

Copies of the foreign references and literature can be found in parent U.S. Application Serial No. 09/811,925.

3. Effect of Information Disclosure Statement (37 C.F.R. § 1.97(h))

This Information Disclosure Statement is not to be construed as a representation that: (i) a search has been made; (ii) additional information material to the examination of this application does not exist; (iii) the information, protocols,

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- . results and the like reported by third parties are accurate or enabling; or (iv) the cited information is, or is considered to be, material to patentability. In addition, applicant does not admit that any enclosed item of information constitutes prior art to the subject invention and specifically reserves the right to demonstrate that any such reference is not prior art.

4. Fee Payment

No fees are believed due because this Information Disclosure Statement is being filed concurrently with the filing of the application.

Respectfully submitted,

Perkins Coie LLP

Date: Oct. 6, 2003

Kenneth H. Ohriner
Kenneth H. Ohriner
Registration No. 31,646

Correspondence Address:

Customer No. 34055
Perkins Coie LLP
Patent – LA
P.O. Box 1208
Seattle, WA 98111-1208
Phone: (310) 788-9900
Fax: (310) 788-3399

EM No. EV 254990096US				COMPLETE IF KNOWN	
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				Group Art Unit	
				Examiner Name	
Sheet	1	of	5	Attorney Docket No.	54008.8012.US04

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	EA	Isagawa, Tatsuhiko, et al., "Ultra Clean Surface Preparation Using Ozonized Ultrapure Water," <i>Extended Abstracts of the 1982 Int'l. Conf. on Solid State Devices and Materials</i> , pp. 193-195 (1992)		
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